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## INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(use as many sheets as necessary)

Complete if Known					
Application Number	09/880,089				
Filing Date	June 14, 2001				
First Named Inventor	Shunpei YAMAZAKI et al.				
Group Art Unit	2818				
Examiner Name	David Vu				
Attorney Docket Number	0756-2325				

				U.S. PATENT DOCUMENT	rs		
Examiner Cite Initials* No.1	U.S. Patent Document  Number Kind Code <sup>2</sup> (if known)		Name of Patentee or Applicant of Cited	Date of Publication of Cited  Document  MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear		
			Document	WIN-DD-1111			
ÞV		5,304,407		Hayashi et al.	04/19/94		
		5,932,893		Miyanaga et al.	08/03/99	C	
	· ·	5,943,560		Chang et al.	08/24/99	28	
		5,977,560		Banerjee et al.	11/02/99		
		6,087,679		Yamazaki et al.	07/11/00	2 F	
		6,107,639		Yamazaki et al.	08/22/00	9 I	
		6,107,654		Yamazaki et al.	08/22/00	E 2	
		6,285,042		Ohtani et al.	09/04/01	2002 LL R	
		6,307,214		Ohtani et al.	10/23/01	00	
		6,307,220		Yamazaki	10/23/01	3	
		6,335,541		Ohtani et al.	01/01/02		
		6,348,368		Yamazaki et al.	02/19/02		
		2002/0008286	A1	Yamazaki et al.	01/24/02		
		2002/0014625	A1	Asami et al.	02/07/02		
<b>—</b>		2002/0038889	A1	Yamazaki et al.	04/04/02		
DV		2002/0043662	A1	Yamazaki et al.	04/18/02		

				FOREIGN PATENT DOC	UMENTS		
Examiner Initials	Cite No.1	Office <sup>3</sup>	Foreign Patent Document  Kind Code  Number <sup>4</sup> (if known)		Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T <sup>6</sup>
DV	+	JР	02-219234	Takaishi	08/31/90		Abst.
1		JP	11-204434	Ohtani et al.	07/30/99		Abst.
	1	JP	11-284198	Yamazaki	10/15/99		Abst.
		JP	11-307783	Yamazaki et al.	11/05/99		Abst.
1		TW	251379		07/11/95		Full
DV		TW	310478		07/11/97		Abst.
			OTHER PR	IOR ART – NON PATENT LITI	ERATURE DOCUMENTS		
Examiner Initials	Cite Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.)., date, page(s), volume-issue number(s), publisher, city and/or country where published.						T <sup>2</sup>
DΥ	Ishihara et al., AM-LCD 99, Microtexture Analysis of Location Controlled Large Si Grain Formed by Excimer-Laser Crystallization Method, July 14, 1999, pp. 99-102						
DV		Late		rature Poly-Si Thin-Film IEEE Electronic Device			

Examiner Signature	Shuland	 , , , , , , ,	Date Considered	11/12/02	4.

<sup>\*</sup>EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.